

driving means including at least another one ~~non-single crystalline~~ thin film transistor for driving the active matrix circuit; and  
at least one ~~single crystalline~~ semiconductor integrated circuit chip for controlling the driving means,

wherein the active matrix circuit, the driving means and the semiconductor integrated circuit chip are formed on the insulating substrate.

4. (Amended) The device of claim 1 wherein the semiconductor integrated circuit chip [has] comprises a central processing unit.

5. (Amended) The device of claim 1 wherein the semiconductor integrated circuit chip [has] comprises a memory.

6. (Amended) The device of claim 1 wherein the substrate [has] comprises a glass substrate.

7. (Amended) A liquid crystal display device comprising:  
a substrate [having] comprising a glass substrate;  
an active matrix circuit including at least one ~~non-single crystalline~~ thin film transistor;  
driving means including at least another one ~~non-single crystalline~~ thin film transistor for driving the active matrix circuit; and  
control means for controlling the driving means, the control means has at least one ~~single crystalline~~ semiconductor integrated circuit chip,  
wherein the active matrix circuit, the driving means and the control means are formed on the substrate.

Please cancel claim 8.

9. (Amended) The device of claim 7 wherein the ~~single crystalline~~ semiconductor integrated circuit chip [has] comprises a central processing unit.

10. (Amended) The device of claim 7 wherein the ~~single crystalline~~ semiconductor integrated circuit chip [has] comprises a memory.

11. (Amended) A liquid crystal display device comprising:  
[a] an insulating substrate;  
an active matrix circuit including at least one non-single crystalline thin film transistor;  
driving means including at least another one non-single crystalline thin film transistor for driving the active matrix circuit; and  
control means for controlling the driving means, the control means being connected with the driving means by a COG (chip on glass),  
wherein the active matrix circuit, the driving means and the control means are formed on the insulating substrate.

12. (Amended) The device of claim 11 wherein the substrate [has] comprises a glass substrate.

13. (Amended) The device of claim 11 wherein the control means has at least one single crystalline semiconductor integrated circuit chip.

14. (Amended) A liquid crystal display device comprising:

[a] an insulating substrate;

an active matrix circuit including at least one non-single crystalline thin film transistor;

driving means including at least another one non-single crystalline thin film transistor for driving the active matrix circuit; and

control means for controlling the driving means, the control means being connected with the driving means by a wire bonding,

wherein the active matrix circuit, the driving means and the control means are formed on the insulating substrate.

15. (Amended) The device of claim 14 wherein the substrate [has] comprises a glass substrate.

16. (Amended) The device of claim 14 wherein the control means has at least one single crystalline semiconductor integrated circuit chip.

17. (Amended) An electric device comprising:

a substrate having an insulating surface;

a plurality of non-single crystalline thin film transistors formed on the [substrate] insulating surface; and

at least one single crystalline semiconductor integrated circuit chip formed on the [substrate] insulating surface,

wherein at least one of the non-single crystalline thin film transistors is provided as an active matrix circuit, at least another one of the non-single crystalline thin film transistors is provided as at least one driving circuit for

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driving the active matrix circuit, and the ~~single crystalline~~ semiconductor integrated circuit chip is provided as a control circuit for controlling the driving circuit.

18. (Amended) The device of claim 17 wherein the substrate [has] comprises a glass substrate.

19. (Amended) The device of claim 17 wherein the ~~single crystalline~~ semiconductor integrated circuit chip is connected with the driving circuit by a wire bonding.

20. (Amended) The device of claim 17 wherein the ~~single crystalline~~ semiconductor integrated circuit chip is connected with the driving circuit by a COG (chip or glass).

21. (Amended) An electric device comprising:  
a pair of insulating substrates opposite to each other;  
an active matrix circuit formed by at least one non-single crystalline thin film transistor;  
a driving circuit formed by at least one other non-single crystalline thin film transistor for driving the active matrix circuit; and  
a single crystalline semiconductor integrated circuit chip,  
wherein the active matrix circuit, the driving circuit and the single crystalline semiconductor integrated circuit are formed on one of the insulating substrate, and

[  
wherein the driving circuit has at least an X-decoder/driver and a Y-decoder/driver [and is formed by at least one thin film transistor].

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22. (Amended) The device of claim 21 wherein the other non-single crystalline thin film transistor is a complementary type.

21.  
23. (Amended) The device of claim 21 wherein the other non-single crystalline thin film transistor has only P-type TFT.

22.  
24. (Amended) The device of claim 21 wherein the other non-single crystalline thin film transistor has only N-type TFT.

25. (Amended) An electric device comprising:  
at least one non-single crystalline thin film transistor forming an active matrix circuit; [and]

at least [another] one other non-single crystalline thin film transistor forming a driver circuit having the substantially same structure as that of the one non-single crystalline thin film transistor[.]; and

a single crystalline semiconductor integrated circuit chip.

wherein the structure includes the same material as at least one of a gate electrode material, a gate insulating material and a channel forming material in the one other non-single crystalline thin film transistor, and

wherein the non-single crystalline thin film transistors and the single crystalline semiconductor integrated circuit chip are formed on the same insulating substrate.

[ Please add the following new claims 26-31:

~~26~~<sup>7</sup>. The device of claim 1 wherein the thin film transistor of the active matrix circuit has the same structure as that of the thin film transistor of the driver circuit.

~~27~~<sup>11</sup>. The device of claim ~~7~~<sup>8</sup> wherein the thin film transistor of the active matrix circuit has the same structure as that of the thin film transistor of the driver circuit.

28. The device of claim 11 wherein the thin film transistor of the active matrix circuit has the same structure as that of the thin film transistor of the driver circuit.

29. The device of claim 14 wherein the thin film transistor of the active matrix circuit has the same structure as that of the thin film transistor of the driver circuit.

~~30~~<sup>18</sup>. The device of claim ~~17~~<sup>14</sup> wherein the thin film transistor of the active matrix circuit has the same structure as that of the thin film transistor of the driver circuit.

~~31~~<sup>23</sup>. The device of claim ~~21~~<sup>19</sup> wherein the thin film transistor of the active matrix circuit has the same structure as that of the thin film transistor of the driver circuit.--